

PLUS Search Results for S/N 09/975,049, Searched June 07, 2002 (Top 50)

5761120	5278087	5561620	6125059	5467308
5633518	5274263	5598369	5511020	5824584
5894148	5585293	5917215	4412311	5886368
6225167	5587947	5838040	6009033	5969383
6225167	5615147	5897354	6218245	4115914
5422292	5687120	5929478	6218245	4334292
5457061	5689459	6072720	6242306	4870470
5625213	5940325	6137728	4868618	5508543
4868619	4336603	5773862	6075724	5905264
5202850	4894802	6071777	5408115	6011725

Most Frequently Occurring Classifications of Patents Returned  
From A Search of 09/975,049 on June 07, 2002

Combined Classifications

15 257/321  
11 257/316  
8 365/185.18  
8 365/185.3  
7 365/185.26  
7 365/185.28  
6 257/314  
6 365/185.29  
5 365/185.33  
5 438/264  
4 438/261  
3 257/324  
3 365/185.01  
3 365/185.09  
3 365/185.12  
3 365/185.14  
3 365/185.22  
3 365/185.27  
3 438/594  
2 257/315  
2 257/319  
2 257/322  
2 257/325  
2 257/326  
2 257/412  
2 365/185.05  
2 365/185.1  
2 365/185.21  
2 365/185.24  
2 365/185.25  
2 365/185.31  
2 365/218  
2 438/257  
2 438/258  
2 438/267  
2 438/275  
2 438/475  
2 438/769  
2 438/775  
2 438/776  
2 438/910  
2 438/911

- 15 257/321 (4 OR, 11 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/314 ..Variable threshold (e.g., floating gate memory device)  
257/315 ...With floating gate electrode  
257/316 ....With additional contacted control electrode  
  
257/321 .....With thin insulator region for charging or discharging floating electrode by quantum mechanical tunneling
- 11 257/316 (3 OR, 8 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/314 ..Variable threshold (e.g., floating gate memory device)  
257/315 ...With floating gate electrode  
257/316 ....With additional contacted control electrode
- 8 365/185.18 (1 OR, 7 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE  
365/185.18 .Particular biasing
- 8 365/185.3 (7 OR, 1 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE  
365/185.18 .Particular biasing  
365/185.29 ..Erase  
365/185.3 ...Over erasure
- 7 365/185.26 (0 OR, 7 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE  
365/185.18 .Particular biasing  
365/185.26 ..Floating electrode (e.g., source, control gate, drain)
- 7 365/185.28 (4 OR, 3 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE  
365/185.18 .Particular biasing  
365/185.28 ..Tunnel programming
- 6 257/314 (4 OR, 2 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/314 ..Variable threshold (e.g., floating gate memory device)

6 365/185.29 (1 OR, 5 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE  
365/185.18 .Particular biasing  
365/185.29 ..Erase

5 365/185.33 (1 OR, 4 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE  
365/185.18 .Particular biasing  
365/185.29 ..Erase  
365/185.33 ...Flash

5 438/264 (1 OR, 4 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF  
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY  
FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS  
438/197 .Having insulated gate (e.g., IGFET, MISFET,  
MOSFET, etc.)  
438/257 ..Having additional gate electrode surrounded  
by dielectric (i.e., floating gate)  
438/264 ...Tunneling insulator

4 438/261 (3 OR, 1 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF  
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY  
FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS  
438/197 .Having insulated gate (e.g., IGFET, MISFET,  
MOSFET, etc.)  
438/257 ..Having additional gate electrode surrounded  
by dielectric (i.e., floating gate)  
438/261 ...Multiple interelectrode dielectrics or  
nonsilicon compound gate insulator

3 257/324 (2 OR, 1 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS  
diode)  
257/314 ..Variable threshold (e.g., floating gate  
memory device)  
257/324 ...Multiple insulator layers (e.g., MNOS  
structure)

3 365/185.01 (2 OR, 1 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE

3 365/185.09 (0 OR, 3 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/185.01 FLOATING GATE  
365/185.05 .Particular connection  
365/185.09 ..Error correction (e.g., redundancy,